

Differentiable Computational Lithography Framework

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Outline



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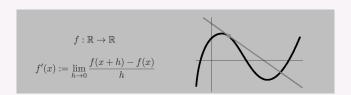
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Differentiable Programming

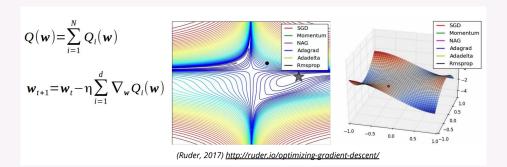
Remember derivatives and gradients?



Derivative



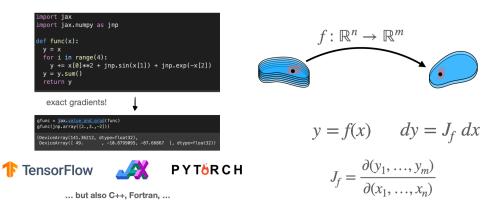
Gradient



Automatic Differentiation



Automatic Differentiation: careful application of chain rule to programs.



Automatic Differentiation = methods for automatically computing gradients of functions specified by a computer program.

Differentiable Programming

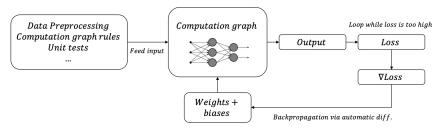


Execute differentiable code via automatic differentiation.

Differentiable programming: Writing software composed of **differentiable and parameterized building blocks** that are executed via **automatic differentiation** and **optimized** in order to perform a specified task.

- A parameterized function (method / model / building blocks) to be optimized;
- 2 Automatic differentiability of the function to be **optimized**.
- 3 A loss to measure performance;

differentiable programming = programming languages + automatic differentiation.



Differentiable programming: master quotes



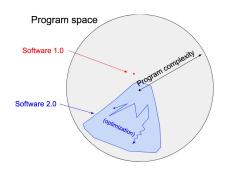


OK, Deep Learning has outlived its usefulness as a buzz-phrase. Deep Learning est mort. Vive Differentiable Programming!

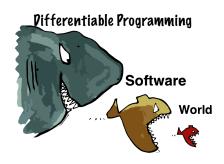


Differentiable programming: Software 2.0





Software 2.0 from Andrej Karpathy¹



AI is eating software from Jensen Huang²

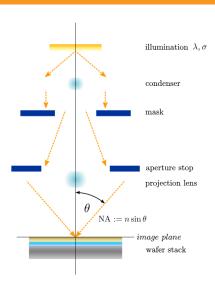
²Software 2.0: https://karpathy.medium.com/software-2-0-a64152b37c35

²AI: https://www.technologyreview.com/ai-is-going-to-eat-software/

Background of Lithography

Lithography





³Tim Fühner. "Artificial Evolution for the Optimization of Lithographic Process Conditions". In: 2014.

The scalar imaging equation



The scalar imaging equation under partially coherent illumination

$$I(x_{1}, y_{1}) = J_{I}((x_{1}, y_{1}), (x_{1}, y_{1}))$$

$$= \iiint \int_{-\infty}^{\infty} J_{C}(x_{0} - x'_{0}, y_{0} - y'_{0}) O(x_{0}, y_{0}) O^{*}(x'_{0}, y'_{0})$$

$$H(x_{1} - x_{0}, y_{1} - y_{0}) H^{*}(x_{1} - x'_{0}, y_{1} - y'_{0}) dx_{0} dy_{0} dx'_{0}dy'_{0},$$
(1)

where O is the object function, the field of the photomask in the lithography case, H is the projector transfer function, and J_C is the mutual intensity, a weight factor, of two points under extended source conditions.

Conclusion

The intensity at a point in the image plane is given by the propagation of the mutual intensity of all contributing points, that is, of all points that lay in the support of the projection system and the illuminator.

Abbe's VS Hopkins'



- Abbe's approach
 - *illumination cross-coefficients (ICC)*

$$ICC(x,y;f,g) = \big| \iint_{-\infty}^{\infty} H(f+f',g+g') \mathcal{F}(M)(f',g') \exp(-j2\pi(f'x+g'y)) \, \mathrm{d}f' \, \mathrm{d}g' \big|^2.$$

Abbe's approach

$$I(x,y) = \iint_{-\infty}^{\infty} J(f,g)ICC(x,y;f,g) df dg.$$

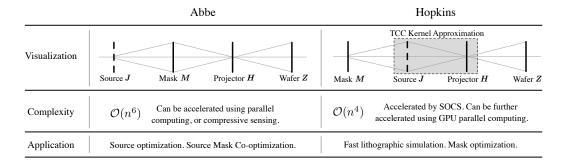
- Hopkins' approach
 - TCC

$$I(x,y) = \iiint_{-\infty}^{\infty} \mathcal{T}(f',g';f'',g'')\mathcal{F}(M)(f',g')\mathcal{F}(M)^*(f'',g'')$$

$$\exp(-j2\pi((f'-f'')x + (g'-g'')y))df'dg'df''dg'',$$

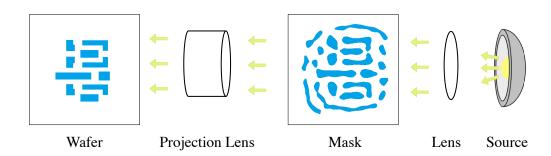
Abbe's VS Hopkins'





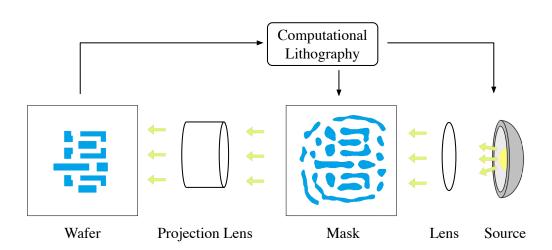
What's next?





Computational Lithography

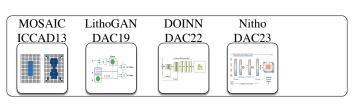


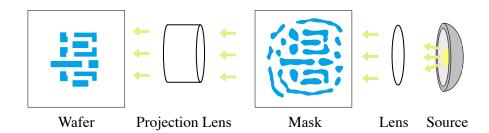


Lithography Modeling



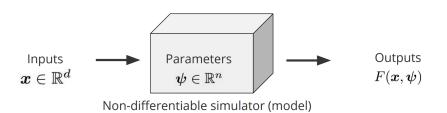






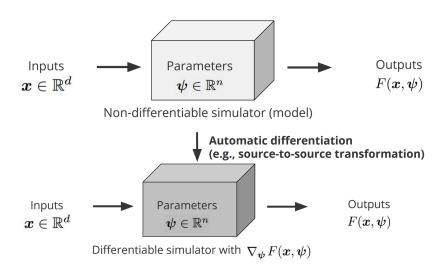
Differentiability without surrogates





Differentiability without surrogates





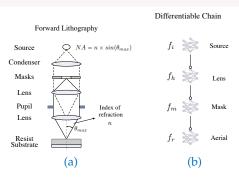
• Use automatic differentiation tools to make the simulator directly differentiable.

From the Tao to the Technique



How can we implement differentiable lithography?

- Complex lithography setups can be composed of a pipeline of a series of distinct modules *i.e.*, source, lens, mask, aerial.
- One might need to differentiate through the whole end-to-end pipeline, which can be achieved by compositionality and the chain rule.



(a) Core components of forward lithography process. (b) The visualization of the differentiable lithography chain.

Differentiable Lithography



Differentiable analysis

• Unify analysis pipeline by simultaneously optimizing the free parameters of an analysis with respect to the desired physics objective.

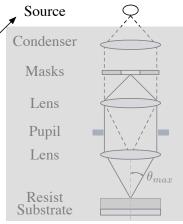
Differentiable simulation

 Enable efficient simulation-based inference, reducing the number of events needed by orders of magnitude.

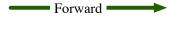
Differentiable Source Module







- 1. Init Parameters
- 2. Calculate source



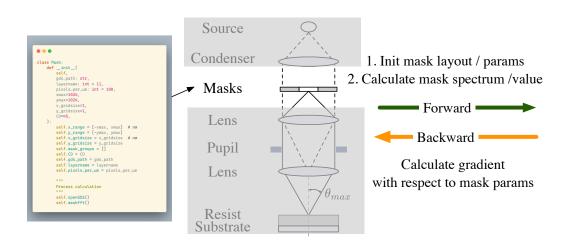


Calculate source gradient with respect to source value

https://github.com/TorchOPC/TorchLitho

Differentiable Mask Module

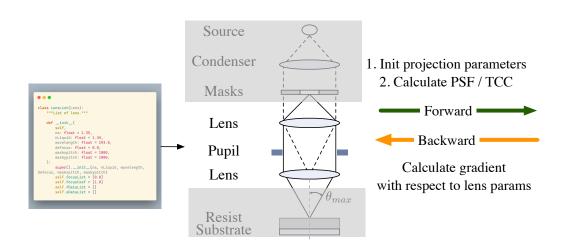




https://github.com/TorchOPC/TorchLitho

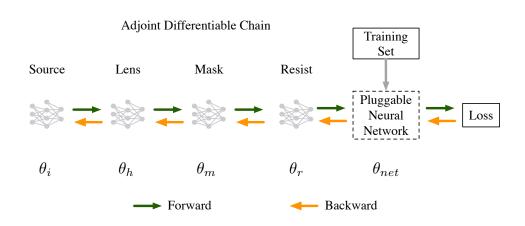
Differentiable Lens Module





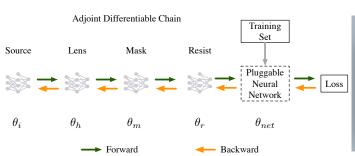
https://github.com/TorchOPC/TorchLitho





Composable Differentiable Lithography



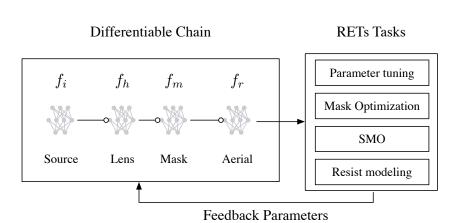


Composable config



Differentiable Lithography Applications





Multi-level optimization framework.



$$\begin{array}{ll} P_n: & \theta_n^* = \operatornamewithlimits{argmin}_{\theta_n} \mathcal{C}_n(\theta_n, \mathcal{U}_n, \mathcal{L}_n; \mathcal{D}_n) & \rhd \operatorname{Level} n \operatorname{problem} \\ & \ddots & \\ P_k: & \operatorname{s.t.} & \theta_k^* = \operatornamewithlimits{argmin}_{\theta_k} \mathcal{C}_k(\theta_k, \mathcal{U}_k, \mathcal{L}_k; \mathcal{D}_k) & \rhd \operatorname{Level} k \in \{2, \dots, n-1\} \operatorname{problem} \\ & \ddots & \\ P_1: & \operatorname{s.t.} & \theta_1^* = \operatornamewithlimits{argmin}_{\theta_k} \mathcal{C}_1(\theta_1, \mathcal{U}_1, \mathcal{L}_1; \mathcal{D}_1) & \rhd \operatorname{Level} 1 \operatorname{problem} \end{array}$$



Source Optimization: optimize source parameters, fix others.

Mask Optimization: optimize mask parameters, fix others.

Source Mask Optimization: bi-level optimization for source and mask

³https://github.com/TorchOPC/TorchLitho



Dataset	DAMO ²¹		TEMPO ³⁴		DOINN ³²		Ours	
	mPA	mIOU	mPA	mIOU	mPA	mIOU	mPA	mIOU
Benchmark1 ³³	95.2	91.1	94.6	88.7	99.19	98.32	99.45	99.21
$\mathrm{Benchmark}2^{35}$	98.97	97.31	98.24	96.55	98.79	97.1	99.15	99.02
$\mathrm{Benchmark}3^{35}$	99.11	93.56	99.06	93.28	99.21	98.41	99.59	99.34
Benchmark4 ^{33, 35}	99.01	97.1	98.63	95.84	98.71	96.68	99.61	99.36
Average	98.07	94.77	97.63	93.59	98.98	97.63	99.45	99.23
Ratio	0.99	0.96	0.98	0.94	0.99	0.98	1	1

The comparison of the proposed method and the SOTA method.

References I



[1] Tim Fühner. "Artificial Evolution for the Optimization of Lithographic Process Conditions". In: 2014.

THANK YOU!